

HIGH-SPEED 3.3V 32K x 18 SYNCHRONOUS PIPELINED DUAL-PORT STATIC RAM

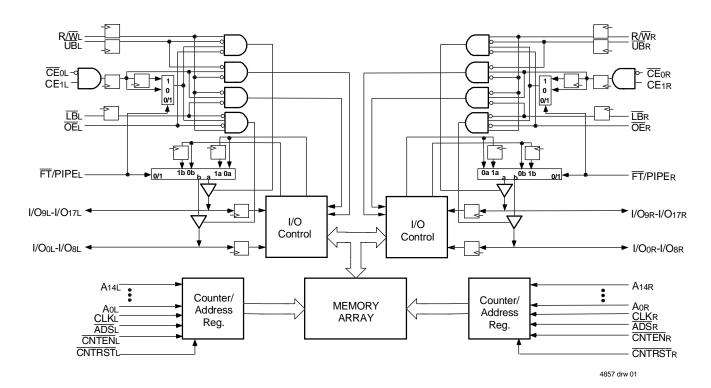
IDT70V9379L

Features:

- True Dual-Ported memory cells which allow simultaneous access of the same memory location
- High-speed clock to data access
 - Commercial: 7.5/9/12ns (max.)
- Low-power operation
 - IDT70V9379L Active: 500mW (typ.) Standby: 1.5mW (typ.)
- ◆ Flow-Through or Pipelined output mode on either port via the FT/PIPE pins
- Counter enable and reset features
- Dual chip enables allow for depth expansion without additional logic

- Full synchronous operation on both ports
 - 4ns setup to clock and 0ns hold on all control, data, and address inputs
 - Data input, address, and control registers
 - Fast 7.5ns clock to data out in the Pipelined output mode
 - Self-timed write allows fast cycle time
 - 12ns cycle time, 83MHz operation in Pipelined output mode
- Separate upper-byte and lower-byte controls for multiplexed bus and bus matching compatibility
- LVTTL- compatible, single 3.3V (±0.3V) power supply
- Industrial temperature range (-40°C to +85°C) is available for selected speeds
- Available in a 128-pin Thin Quad Flatpack (TQFP)

Functional Block Diagram



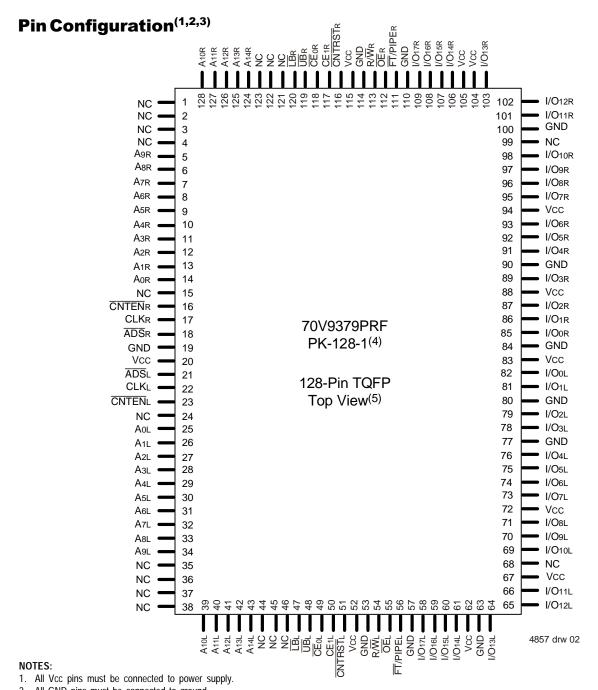
JANUARY 2001

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Description:

The IDT70V9379 is a high-speed 32K x 18 bit synchronous Dual-Port RAM. The memory array utilizes Dual-Port memory cells to allow simultaneous access of any address from both ports. Registers on control, data, and address inputs provide minimal setup and hold times. The timing latitude provided by this approach allows systems to be designed with very short cycle times.

With an input data register, the IDT70V9379 has been optimized for applications having unidirectional or bidirectional data flow in bursts. An automatic power down feature, controlled by $\overline{\text{CE}}_0$ and CE₁, permits the on-chip circuitry of each port to enter a very low standby power mode. Fabricated using IDT's CMOS high-performance technology, these devices typically operate on only 500mW of power.



- All GND pins must be connected to ground.
- Package body is approximately 14mm x 20mm x 1.4mm.
- This package code is used to reference the package diagram.
- This text does not indicate orientation of the actual part-marking.

Pin Names

Left Port	Right Port	Names			
CEOL, CE1L	CEOR, CE1R	Chip Enables			
R/WL	R/W̄R	Read/Write Enable			
ŌĒL	OE R	Output Enable			
A0L - A14L	A0R - A14R	Address			
I/O ₀ L - I/O ₁₇ L	I/Oor - I/O17R	Data Input/Output			
CLKL	CLKR	Clock			
ŪB∟	ŪBR	Upper Byte Select			
LB L	IB R	Lower Byte Select			
AD SL	AD SR	Address Strobe Enable			
CNTENL	<u>CNTEN</u> R	Counter Enable			
CNTRSTL	<u>CNTRST</u> R	Counter Reset			
FT/PIPEL	FT/PIPER	Flow-Through / Pipeline			
V	CC	Power			
Gl	ND	Ground			

4857 tbl 01

Truth Table I—Read/Write and Enable Control(1,2,3)

ŌĒ	CLK	Œ₀	CE ₁	ŪB	<u>ГВ</u>	R/W	Upper Byte I/O ₉₋₁₇	Lower Byte I/O ₀₋₈	MODE
Х	\uparrow	Н	Χ	Х	Χ	Х	High-Z	High-Z	Deselected-Power Down
Х	\uparrow	Χ	L	Χ	Χ	Х	High-Z	High-Z	Deselected-Power Down
Х	\uparrow	L	Н	Н	Н	Χ	High-Z	High-Z	Both Bytes Deselected
Х	\uparrow	L	Н	L	Н	L	DATAIN	High-Z	Write to Upper Byte Only
Х	\uparrow	L	Н	Н	L	L	High-Z	DATAIN	Write to Lower Byte Only
Х	\uparrow	L	Н	L	L	L	DATAIN	DATAIN	Write to Both Bytes
L	\uparrow	L	Н	L	Н	Н	DATA out	High-Z	Read Upper Byte Only
L	\uparrow	L	Н	Н	L	Н	High-Z	DATA _{OUT}	Read Lower Byte Only
L	\uparrow	L	Н	L	L	Н	DATA out	DATAout	Read Both Bytes
Н	Χ	L	Н	L	L	Χ	High-Z	High-Z	Outputs Disabled

4857 tbl 02 NOTES:

- "H" = V_{IH}, "L" = V_{IL}, "X" = Don't Care.
 ADS, CNTEN, CNTRST = X.
 OE is an asynchronous input signal.

Truth Table II—Address Counter Control (1,2,6)

Address	Previous Address	Addr Used	CLK	ĀDS	CNTEN	CNTRST	I/O ⁽³⁾	MODE
Х	Х	0	↑	Х	Х	L	Dvo(0)	Counter Reset to Address 0
An	Х	An	1	L ⁽⁴⁾	Х	Н	Dvo(n)	External Address Loaded into Counter
An	Ар	Ар	↑	Н	Н	Н	Dvo(p)	External Address Blocked—Counter disabled (Ap reused)
Х	Ар	Ap + 1	1	Н	L ⁽⁵⁾	Н	Dvo(p+1)	Counter Enabled—Internal Address generation

NOTES:

4857 tbl 03

- 1. "H" = VIH, "L" = VIL, "X" = Don't Care.
- 2. \overline{CE}_0 , \overline{LB} , \overline{UB} , and $\overline{OE} = VIL$; \overline{CE}_1 and $\overline{R}/\overline{W} = VIH$.
- 3. Outputs configured in Flow-Through Output mode; if outputs are in Pipelined mode the data out will be delayed by one cycle.
- 4. ADS is independent of all other signals including CEo, CE1, UB and LB.
- 5. The address counter advances if ONTEN = VIL on the rising edge of CLK, regardless of all other signals including OEo, CE1, UB and UB.
- 6. While an external address is being loaded ($\overline{ADS} = VIL$), $R/\overline{W} = VIH$ is recommended to ensure data is not written arbitrarily.

Recommended Operating Temperature and Supply Voltage⁽¹⁾

Grade	Ambient Temperature ⁽²⁾	GND	Vcc
Commercial	0°C to +70°C	0V	3.3V <u>+</u> 0.3V
Industrial	-40°C to +85°C	0V	3.3V <u>+</u> 0.3V

NOTES:

4857 thl 04

- Industrial temperature: for specific speeds, packages and powers contact your sales office.
- 2. This is the parameter Ta. This is the "instant on" case temperature.

Recommended DC Operating Conditions

Symbol	Parameter	Min.	Тур.	Мах.	Unit
Vcc	Supply Voltage	3.0	3.3	3.6	V
GND	Ground	0	0	0	V
VIH	Input High Voltage	2.0V	_	Vcc+0.3V ⁽²⁾	V
VIL	Input Low Voltage	-0.3 ⁽¹⁾	_	0.8	٧

4857 tbl 05

NOTES:

- 1. VIL > -1.5V for pulse width less than 10 ns.
- 2. VTERM must not exceed Vcc +0.3V.

Absolute Maximum Ratings⁽¹⁾

Symbol	Rating	Commercial & Industrial	Unit
VTERM ⁽²⁾	Terminal Voltage with Respect to GND	-0.5 to +4.6	V
TBIAS	Temperature Under Bias	-55 to +125	°C
Tstg	Storage Temperature	-55 to +150	°C
ЮИТ	DC Output Current	50	mA

NOTES:

4857 tbl 06

- Stresses greater than those listed under ABSOLUTE MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.
- 2. VTERM must not exceed Vcc +0.3V for more than 25% of the cycle time or 10ns maximum, and is limited to \leq 20mA for the period of VTERM \geq Vcc + 0.3V.

Capacitance⁽¹⁾ (TA = +25°C, f = 1.0MHz)

Syn	nbol	Parameter	Conditions ⁽²⁾	Max.	Unit
С	;IN	Input Capacitance	$V_{IN} = 3dV$	9	pF
Со	UT ⁽³⁾	Output Capacitance	Vout = 3dV	10	pF

NOTES:

- These parameters are determined by device characterization, but are not production tested.
- 3dV references the interpolated capacitance when the input and output switch from 0V to 3V or from 3V to 0V.
- 3. Cout also references C_{1/0}.

DC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range (Vcc = 3.3V ± 0.3V)

			70V9379L		
Symbol	Parameter	Test Conditions		Max.	Unit
ILI	Input Leakage Current ⁽¹⁾	Vcc = 3.6V, $VIN = 0V$ to Vcc	_	5	μA
ILO	Output Leakage Current	\overline{CE} = VIH or CE1 = VIL, VOUT = 0V to VCC	ı	5	μA
Vol	Output Low Voltage	IOL = +4mA	-	0.4	V
Vон	Output High Voltage	IOH = -4mA	2.4	_	V

NOTE:

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DC Electrical Characteristics Over the Operating Temperature Supply Voltage Range $^{(3,6)}$ (Vcc = 3.3V ± 0.3V)

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						379L7 I Only		379L9 Only		379L12 Only	
Symbol	Parameter	Test Condition	Versio	n	Тур.(4)	Max.	Тур.(4)	Max.	Typ. ⁽⁴⁾	Max.	Unit
lcc	Dynamic Operating Current (Both	CEL and CER= VIL,	COM'L	L	200	310	180	260	150	230	mA
	Ports Active)	Outputs Disabled, f = fMAX ⁽¹⁾	IND	L		_	_	_	_	_	
ISB1	Standby Current	ŒL = ŒR = VH	COM'L	L	65	130	50	100	40	80	mA
	(Both Ports - TTL Level Inputs)	$f = fMAX^{(1)}$	IND	L	_	_	_	_	_	_	
ISB2	Standby		COM'L	L	140	245	110	190	100	175	mA
Current (One Port - TTL Level Inputs)	Port - TTL	CE"B" = VIH ⁽⁵⁾ Active Port Outputs Disabled, f=fMAX ⁽¹⁾	IND	L	_	_	_	_	_	_	
ISB3	Full Standby	Both Ports CEL and	COM'L	L	0.4	3	0.4	3	0.4	3	mA
	Current (Both Ports - CMOS Level Inputs)	$\overline{CER} \ge VCC - 0.2V$, $VIN \ge VCC - 0.2V$ or $VIN \le 0.2V$, $f = 0^{(2)}$	IND	L	_	-	_	_		_	
ISB4	Full Standby	\overline{CE} "A" $\leq 0.2V$ and	COM'L	L	130	235	100	180	90	165	mA
	Current (One Port - CMOS Level Inputs)	$\begin{array}{l} \overline{\text{CE}}\text{`B"} \geq \text{VCC} - 0.2\text{V}^{(5)} \\ \text{VN} \geq \text{VCC} - 0.2\text{V or} \\ \text{VN} \leq 0.2\text{V}, \text{ Active Port,} \\ \text{Outputs Disabled, } f = \text{fMAX}^{(1)} \end{array}$	IND	L				_		_	

NOTES:

- 1. At f = fmax, address and control lines (except Output Enable) are cycling at the maximum frequency clock cycle of 1/tcyc, using "AC TEST CONDITIONS" at input levels of GND to 3V.
- 2. f = 0 means no address, clock, or control lines change. Applies only to input at CMOS level standby.
- 3. Port "A" may be either left or right port. Port "B" is the opposite from port "A".
- 4. Vcc = 3.3V, TA = 25°C for Typ, and are not production tested. lcc pc(f=0) = 90mA (Typ).
- 5. $\overline{CE}x = V_{IL} \text{ means } \overline{CE}_{0x} = V_{IL} \text{ and } CE_{1x} = V_{IH}$
 - $\overline{CE}x = VIH \text{ means } \overline{CE}_{0}x = VIH \text{ or } CE_{1}x = VIL$
 - $\overline{\text{CE}}\text{x} \leq 0.2 V$ means $\overline{\text{CE}}\text{ox} \leq \underline{0}.2 V$ and $\text{CE}\text{1x} \geq V\text{cc}$ 0.2 V
 - $\overline{\text{CE}}\text{x} \geq \text{Vcc}$ 0.2V means $\overline{\text{CE}}\text{ox} \geq \text{Vcc}$ 0.2V or $\text{CE}\text{1x} \leq 0.2\text{V}$
 - "X" represents "L" for left port or "R" for right port.
- 6. Industrial temperature: for specific speeds, packages and powers contact your sales office.

^{1.} At Vcc ≤ 2.0V input leakages are undefined.

AC Test Conditions

Input Pulse Levels	GND to 3.0V
Input Rise/Fall Times	3ns Max.
Input Timing Reference Levels	1.5V
Output Reference Levels	1.5V
Output Load	Figures 1, 2, and 3

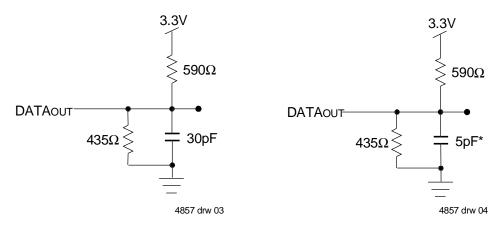


Figure 1. AC Output Test load.

Figure 2. Output Test Load (For tcklz, tckHz, tolz, and toHz). *Including scope and jig.

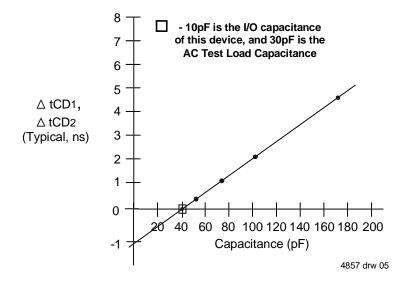


Figure 3. Typical Output Derating (Lumped Capacitive Load).

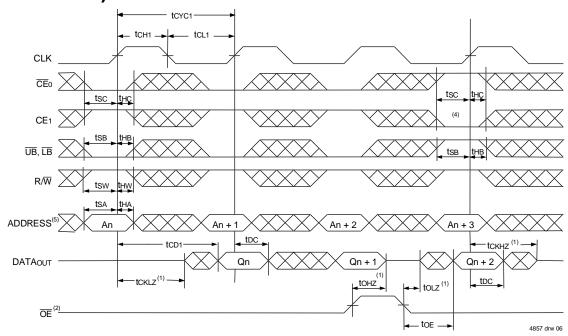
AC Electrical Characteristics Over the Operating Temperature Range (Read and Write Cycle Timing) $^{(3,4)}$ (Vcc = 3.3V ± 0.3V, TA = 0°C to +70°C)

		70V9 Com'	379L7 I Only	70V9 Com'	379L9 I Only	70V9 Com		
Symbol	Parameter	Min.	Max.	Min.	Max.	Min.	Max.	Unit
tcyc1	Clock Cycle Time (Flow-Through) ⁽²⁾	22		25	_	30	_	ns
tcyc2	Clock Cycle Time (Pipelined) ⁽²⁾	12		15	_	20	_	ns
tch1	Clock High Time (Flow-Through) ⁽²⁾	7.5		12	_	12	_	ns
ta_1	Clock Low Time (Flow-Through) ⁽²⁾	7.5	_	12	_	12	_	ns
tCH2	Clock High Time (Pipelined) ⁽²⁾	5		6	_	8	_	ns
tal2	Clock Low Time (Pipelined) ⁽²⁾	5	_	6	_	8	_	ns
t _R	Clock Rise Time	_	3		3	_	3	ns
tF	Clock Fall Time	_	3		3	_	3	ns
tsa	Address Setup Time	4		4	_	4	_	ns
tha	Address Hold Time	0		1	_	1	_	ns
tsc	Chip Enable Setup Time	4		4	_	4	_	ns
thc	Chip Enable Hold Time	0	_	1	_	1	_	ns
tsw	R/W Setup Time	4	_	4	_	4	_	ns
thw	R/W Hold Time	0		1	_	1	_	ns
tsd	Input Data Setup Time	4		4	_	4	_	ns
thd	Input Data Hold Time	0	_	1	_	1	_	ns
tsad	ADS Setup Time	4	_	4	_	4	_	ns
thad	ADS Hold Time	0		1	_	1	_	ns
tscn	CNTEN Setup Time	4		4	_	4		ns
thon	CNTEN Hold Time	0	_	1	_	1	_	ns
tsrst	CNTRST Setup Time	4		4	_	4		ns
thrst	CNTRST Hold Time	0	_	1	_	1	_	ns
toe	Output Enable to Data Valid	_	9	_	12	_	12	ns
tolz	Output Enable to Output Low-Z ⁽¹⁾	2		2	_	2	_	ns
tонz	Output Enable to Output High-Z ⁽¹⁾	1	7	1	7	1	7	ns
tCD1	Clock to Data Valid (Flow-Through) ⁽²⁾	_	18		20	_	25	ns
tCD2	Clock to Data Valid (Pipelined) ⁽²⁾	_	7.5		9	_	12	ns
toc	Data Output Hold After Clock High	2		2	_	2	_	ns
tckhz	Clock High to Output High-Z ⁽¹⁾	2	9	2	9	2	9	ns
tcklz	Clock High to Output Low-Z ⁽¹⁾	2	_	2	_	2	_	ns
Port-to-Port I	Delay	•	-	<u>-</u>	<u>-</u>	-	-	
tcwdd	Write Port Clock High to Read Data Delay	_	28		35	_	40	ns
tccs	Clock-to-Clock Setup Time		10		15	_	15	ns

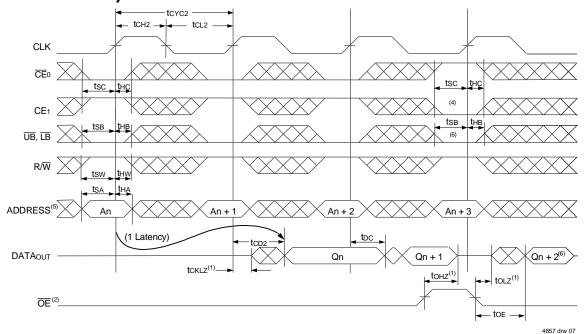
NOTES:

- 1. Transition is measured 0mV from Low or High-impedance voltage with the Output Test Load (Figure 2). This parameter is guaranteed by device characterization, but is not production tested.
- 2. The Pipelined output parameters (tcyc2, tcb2) apply to either or both the Left and Right ports when FT/PIPE = VIH. Flow-through parameters (tcyc1, tcb1) apply when FT/PIPE = VIL for that port.
- 3. All input signals are synchronous with respect to the clock except for the asynchronous Output Enable (OE), FT/PIPER, and FT/PIPEL.
- 4. Industrial temperature: for specific speeds, packages and powers contact your sales office.

Timing Waveform of Read Cycle for Flow-Through Output $(\overline{FT}/PIPE"x" = VIL)^{(3,7)}$

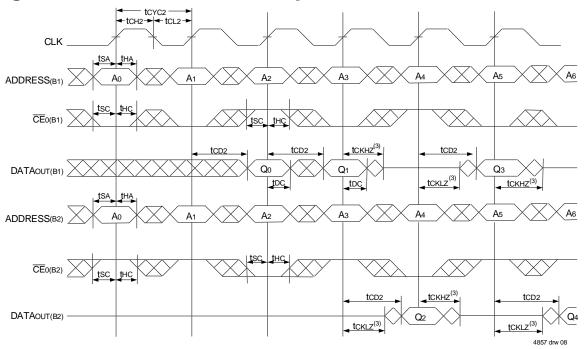


Timing Waveform of Read Cycle for Pipelined Operation $(\overline{FT}/PIPE"x" = Vih)^{(3,7)}$

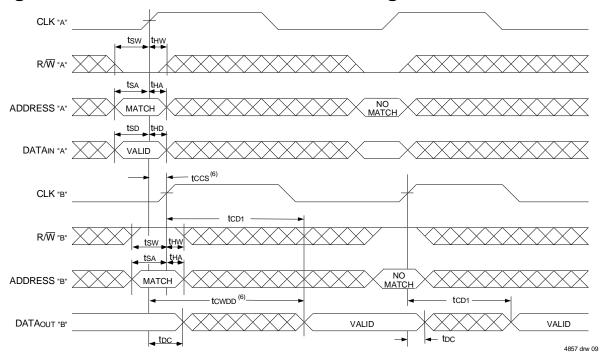


- NOTES:
- 1. Transition is measured 0mV from Low or High-impedance voltage with the Output Test Load (Figure 2).
- 2. $\overline{\text{OE}}$ is asynchronously controlled; all other inputs are synchronous to the rising clock edge.
- 3. $\overline{ADS} = VIL$, \overline{CNTEN} and $\overline{CNTRST} = VIH$.
- 4. The output is disabled (High-Impedance state) by $\overline{\text{CE}}_0 = \text{V}_{\text{IH}}$, $\overline{\text{CE}}_1 = \text{V}_{\text{IL}}$, $\overline{\text{UB}} = \text{V}_{\text{IH}}$, or $\overline{\text{LB}} = \text{V}_{\text{IH}}$ following the next rising edge of the clock. Refer to Truth Table 1.
- 5. Addresses do not have to be accessed sequentially since ADS = VIL constantly loads the address on the rising edge of the CLK; numbers are for reference use only.
- 6. If UB or LB was HIGH, then the Upper Byte and/or Lower Byte of DATAouT for Qn + 2 would be disabled (High-Impedance state).
- 7. "X' here denotes Left or Right port. The diagram is with respect to that port.

Timing Waveform of a Bank Select Pipelined Read (1,2)

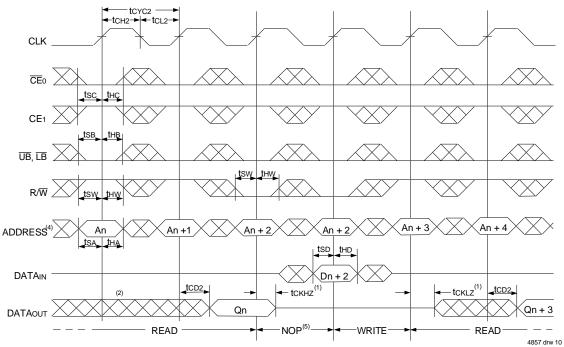


Timing Waveform with Port-to-Port Flow-Through Read^(4,5,7)

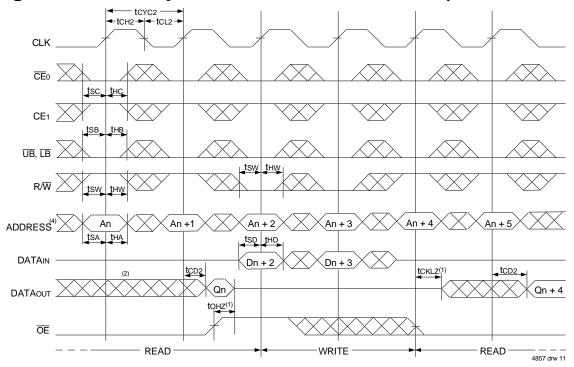


- 1. B1 Represents Bank #1; B2 Represents Bank #2. Each Bank consists of one IDT70V9379 for this waveform, and are setup for depth expansion in this example. ADDRESS(B1) = ADDRESS(B2) in this situation.
- 2. $\overline{\text{UB}}$, $\overline{\text{LB}}$, $\overline{\text{OE}}$, and $\overline{\text{ADS}}$ = VIL; CE1(B1), CE1(B2), R/W, CNTEN, and CNTRST = VIH.
- 3. Transition is measured 0mV from Low or High-impedance voltage with the Output Test Load (Figure 2).
- 4. \(\overline{CE}_0, \overline{UB}, \overline{LB}, \) and \(\overline{ADS} = VIL; \) CE1, \(\overline{CNTEN}, \) and \(\overline{CNTRST} = VIH. \)
 5. \(\overline{OE} = VIL \) for the Right Port, which is being read from. \(\overline{OE} = VIH \) for the Left Port, which is being written to.
- 6. If tccs ≤ maximum specified, then data from right port READ is not valid until the maximum specified for tcwdd. If tccs > maximum specified, then data from right port READ is not valid until tccs + tcp1. tcwbb does not apply in this case.
- 7. All timing is the same for both Left and Right ports. Port "A" may be either Left or Right port. Port "B" is the opposite from Port "A".

Timing Waveform of Pipelined Read-to-Write-to-Read (\overline{OE} = V_{IL})⁽³⁾

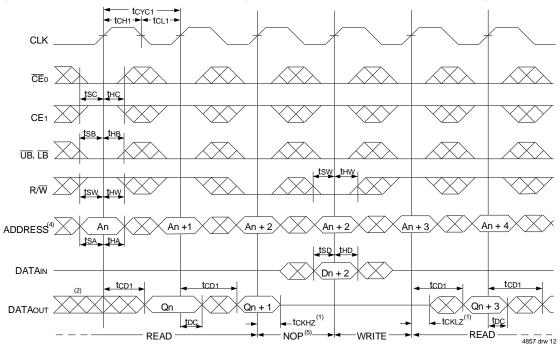


Timing Waveform of Pipelined Read-to-Write-to-Read (OE Controlled)(3)

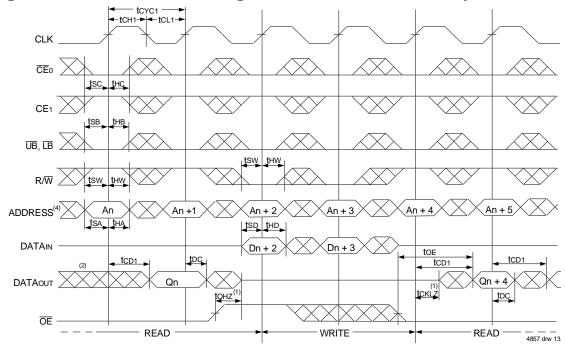


- 1. Transition is measured 0mV from Low or High-impedance voltage with the Output Test Load (Figure 2).
- 2. Output state (High, Low, or High-impedance) is determined by the previous cycle control signals.
- 3. $\overline{CE_0}$, \overline{UB} , \overline{LB} , and \overline{ADS} = VIL; $\overline{CE_1}$, \overline{CNTEN} , and \overline{CNTRST} = VIH. "NOP" is "No Operation".
- 4. Addresses do not have to be accessed sequentially since ADS = VIL constantly loads the address on the rising edge of the CLK; numbers are for reference use only.
- 5. "NOP" is "No Operation." Data in memory at the selected address may be corrupted and should be re-written to guarantee data integrity.

Timing Waveform of Flow-Through Read-to-Write-to-Read $(\overline{OE} = V_{IL})^{(3)}$

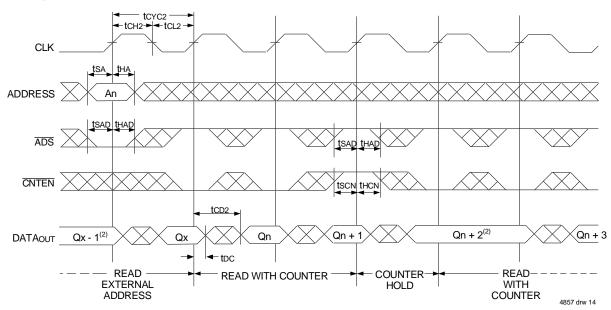


Timing Waveform of Flow-Through Read-to-Write-to-Read (OE Controlled)(3)

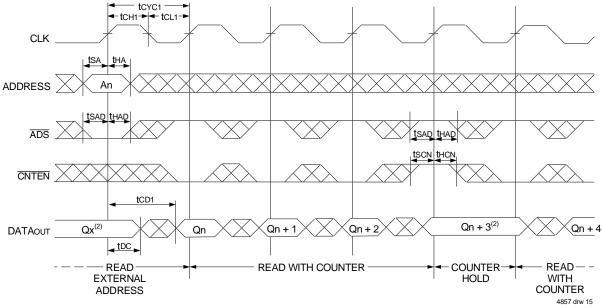


- 1. Transition is measured 0mV from Low or High-impedance voltage with the Output Test Load (Figure 2).
- 2. Output state (High, Low, or High-impedance) is determined by the previous cycle control signals.
- 3. \overline{CE}_0 , \overline{UB} , \overline{LB} , and \overline{ADS} = V_{IL}; \overline{CE}_1 , \overline{CNTEN} , and \overline{CNTRST} = V_{IH}. "NOP" is "No Operation".
- Addresses do not have to be accessed sequentially since ADS = VIL constantly loads the address on the rising edge of the CLK; numbers are for reference use only.
- 5. "NOP" is "No Operation." Data in memory at the selected address may be corrupted and should be re-written to guarantee data integrity.

Timing Waveform of Pipelined Read with Address Counter Advance⁽¹⁾

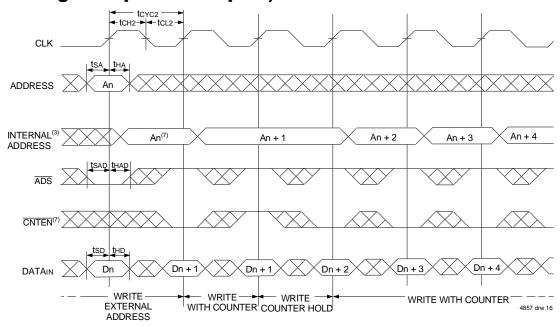


Timing Waveform of Flow-Through Read with Address Counter Advance $^{(1)}$

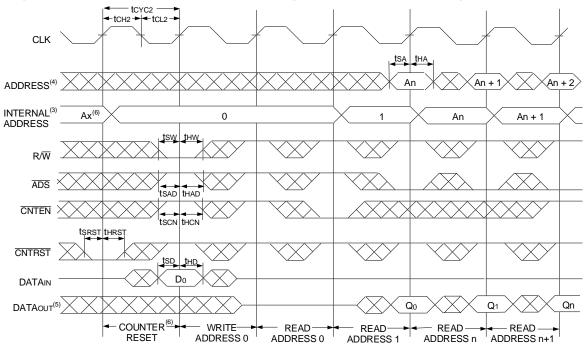


- 1. \overline{CE}_0 , \overline{OE} , \overline{UB} , and \overline{LB} = VIL; CE1, R/ \overline{W} , and \overline{CNTRST} = VIH.
- 2. If there is no address change via $\overline{ADS} = VIL$ (loading a new address) or $\overline{CNTEN} = VIL$ (advancing the address), i.e. $\overline{ADS} = VIH$ and $\overline{CNTEN} = VIH$, then the data output remains constant for subsequent clocks.

Timing Waveform of Write with Address Counter Advance (Flow-Through or Pipelined Outputs)⁽¹⁾



Timing Waveform of Counter Reset (Pipelined Outputs)(2)



- 1. \overline{CE}_0 , \overline{UB} , \overline{LB} , and $R/\overline{W} = V_{IL}$; CE_1 and $\overline{CNTRST} = V_{IH}$.
- 2. \overline{CE}_0 , \overline{UB} , \overline{LB} = VIL; CE1 = VIH.
- 3. The "Internal Address" is equal to the "External Address" when ADS = VIL and equals the counter output when ADS = VIH.
- 4. Addresses do not have to be accessed sequentially since $\overline{ADS} = V_{1L}$ constantly loads the address on the rising edge of the CLK; numbers are for reference use only.
- 5. Output state (High, Low, or High-impedance) is determined by the previous cycle control signals.
- 6. No dead cycle exists during counter reset. A READ or WRITE cycle may be coincidental with the counter reset cycle. ADDRo will be accessed. Extra cycles are shown here simply for clarification.
- 7. CNTEN = VIL advances Internal Address from 'An' to 'An +1'. The transition shown indicates the time required for the counter to advance.
 The 'An +1' Address is written to during this cycle.

Functional Description

The IDT70V9379 provides a true synchronous Dual-Port Static RAM interface. Registered inputs provide minimal set-up and hold times on address, data, and all critical control inputs. All internal registers are clocked on the rising edge of the clock signal, however, the self-timed internal write pulse is independent of the LOW to HIGH transition of the clock signal.

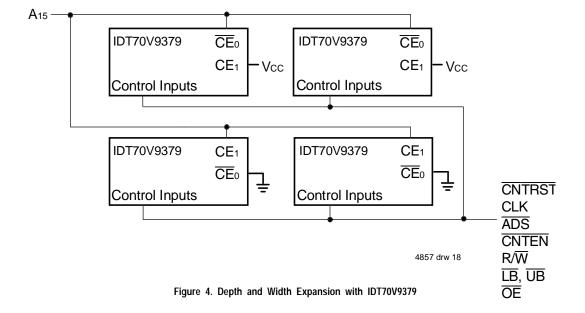
An asynchronous output enable is provided to ease asynchronous bus interfacing. Counter enable inputs are also provided to staff the operation of the address counters for fast interleaved memory applications.

 $\overline{\text{CE}}_0 = \text{VIL}$ and $\text{CE}_1 = \text{VIH}$ for one clock cycle will power down the internal circuitry to reduce static power consumption. Multiple chip enables allow easier banking of multiple IDT70V9379's for depth expansion configurations. When the Pipelined output mode is enabled, two cycles are required with $\overline{\text{CE}}_0 = \text{VIL}$ and $\text{CE}_1 = \text{VIH}$ to re-activate the outputs.

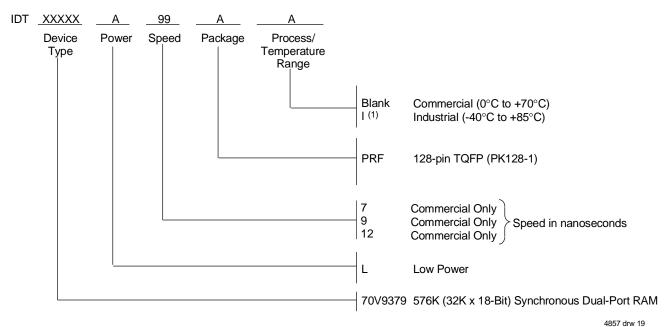
Depth and Width Expansion

The IDT70V9379 features dual chip enables (refer to Truth Table I) inorder to facilitate rapid and simple depth expansion with no requirements for external logic. Figure 4 illustrates how to control the various chip enables in order to expand two devices in depth.

The IDT70V9379 can also be used in applications requiring expanded width, as indicated in Figure 4. Since the banks are allocated at the discretion of the user, the external controller can be set up to drive the input signals for the various devices as required to allow for 36-bit or wider applications.



Ordering Information



NOTE:

1. Industrial temperature range is available.

For specific speeds, packages and powers contact your sales office.

Datasheet Document History

9/30/99: Initial Public Release 11/10/99: Replace IDT logo

1/17/01: Page 4 Changed information in Truth Table II

Increased storage temperature parameters

Clarified Taparameter

Page 5 DC Electrical parameters-changed wording from "open" to "disabled"

Changed ±200mV to 0mV in notes Removed Preliminary status



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